

**Preliminary Information**

August 1994

**Description**

The μPD431132L is a 32,768-word by 32-bit synchronous static RAM fabricated with advanced CMOS technology. Its unique peripheral circuits and N-channel memory cells make the μPD431132L suitable in low-voltage applications requiring high speed, high density, and wide bit configurations such as cache and buffer memory.

**Features**

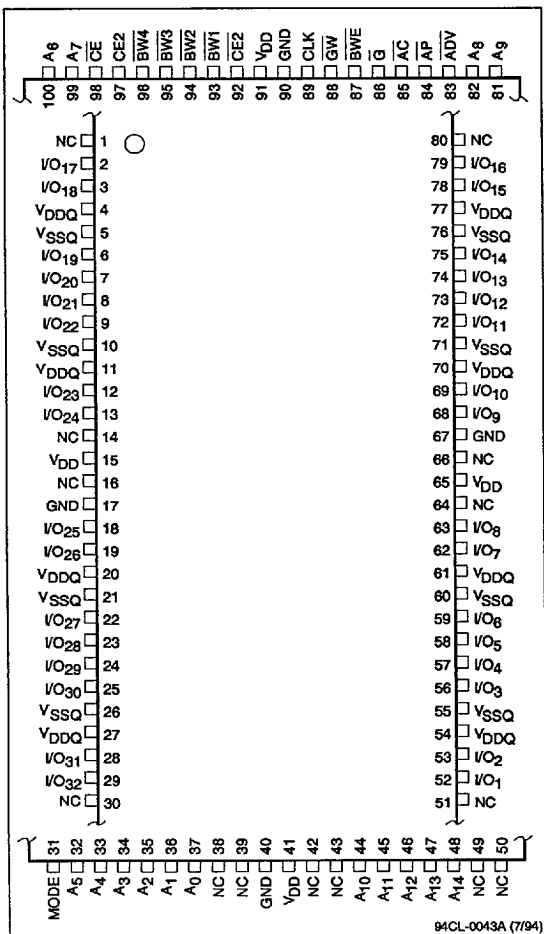
- Single +3.3-volt power supply
- Synchronous operation
- Burst read/write selectable at MODE pin
  - Pentium™ burst sequence
  - Linear burst sequence
- Fully registered inputs
- Registers triggered off positive clock edge
- LVTTL-compatible inputs and outputs
- 5-volt tolerant I/O
- Common I/O using three-state outputs
- Three chip enables for easy depth expansion: pins  $\overline{CE}$ ,  $\overline{CE2}$ ,  $\overline{CE2}$
- Byte write enables: pins  $\overline{BW1}$  -  $\overline{BW4}$  and  $\overline{BWE}$
- Global write enable: pin  $\overline{GW}$
- Asynchronous output enable: pin  $\overline{G}$
- Fast clock access time
  - 10 ns at 60 MHz
  - 12 ns at 50 MHz
  - 14 ns at 50 MHz
- 100-pin TQFP package

**Ordering Information**

Part Number	Access Time (max)	Package
μPD431132LGF-10	10 ns	100-pin TQFP
GF-12	12 ns	
GF-14	14 ns	

**Pin Configuration**

**100-Pin TQFP**



94CL-0043A (7/94)

Pentium is a trademark of Intel Corporation.

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**Pin Identification**

Symbol	Function
A <sub>0</sub> - A <sub>14</sub>	Address input
I/O <sub>1</sub> - I/O <sub>32</sub>	Data input and output
ADV	Burst address advance
AC	Controller address status
AP	Processor address status
CE, CE2, CE2	Chip enable
BW1 - BW4, BWE	Byte write enable
G	Output enable
GW	Global write
MODE	Mode select
CLK	System clock input
V <sub>DD</sub>	+3.3-volt power
GND	Ground
V <sub>DDQ</sub>	Power for outputs
V <sub>SSQ</sub>	Ground for outputs

**Pentium Burst Sequence † \***

External address	A <sub>14</sub> - A <sub>2</sub> , A <sub>1</sub> , A <sub>0</sub>
1st burst address	A <sub>14</sub> - A <sub>2</sub> , A <sub>1</sub> , A <sub>0</sub>
2nd burst address	A <sub>14</sub> - A <sub>2</sub> , A <sub>1</sub> , A <sub>0</sub>
3rd burst address	A <sub>14</sub> - A <sub>2</sub> , A <sub>1</sub> , A <sub>0</sub>

† MODE pin = NC or V<sub>DD</sub>

\* The burst sequence wraps around to its initial state upon completion.

**Linear Burst Sequence † \***

External address	A, 0, 0	A, 0, 1	A, 1, 0	A, 1, 1
1st burst address	A, 0, 1	A, 1, 0	A, 1, 1	A, 0, 0
2nd burst address	A, 1, 0	A, 1, 1	A, 0, 0	A, 0, 1
3rd burst address	A, 1, 1	A, 0, 0	A, 0, 1	A, 1, 0

† MODE pin = GND

\* The burst sequence wraps around to its initial state upon completion. A = A<sub>14</sub> - A<sub>2</sub>

**Synchronous Truth Table**

Operation	CE	CE2	CE2	AP	AC	ADV	† Write	CLK	Address
Deselected	H	X	X	X	L	X	X	L-H	N/A
	L	X	L	L	X	X	X	L-H	N/A
	L	H	X	L	X	X	X	L-H	N/A
	L	X	L	H	L	X	X	L-H	N/A
	L	H	X	H	L	X	X	L-H	N/A
Read Cycle									
Begin burst	L	L	H	L	X	X	X	L-H	External
Begin burst	L	L	H	H	L	X	H	L-H	External
Continue burst	X	X	X	H	H	L	H	L-H	Next
Continue burst	H	X	X	X	H	L	H	L-H	Next
Suspend burst	X	X	X	H	H	H	H	L-H	Current
Suspend burst	H	X	X	X	H	H	H	L-H	Current
Write Cycle									
Begin burst	L	L	H	H	L	X	L	L-H	External
Continue burst	X	X	X	H	H	L	L	L-H	Next
Continue burst	H	X	X	X	H	L	L	L-H	Next
Suspend burst	X	X	X	H	H	H	L	L-H	Current
Suspend burst	H	X	X	X	H	H	L	L-H	Current

† In the Write column, L means one or more byte write enables (BW1 - BW4) and BWE are low, or GW is low. H means all byte write enables are high.

\* X means don't care.

### Asynchronous Truth Table

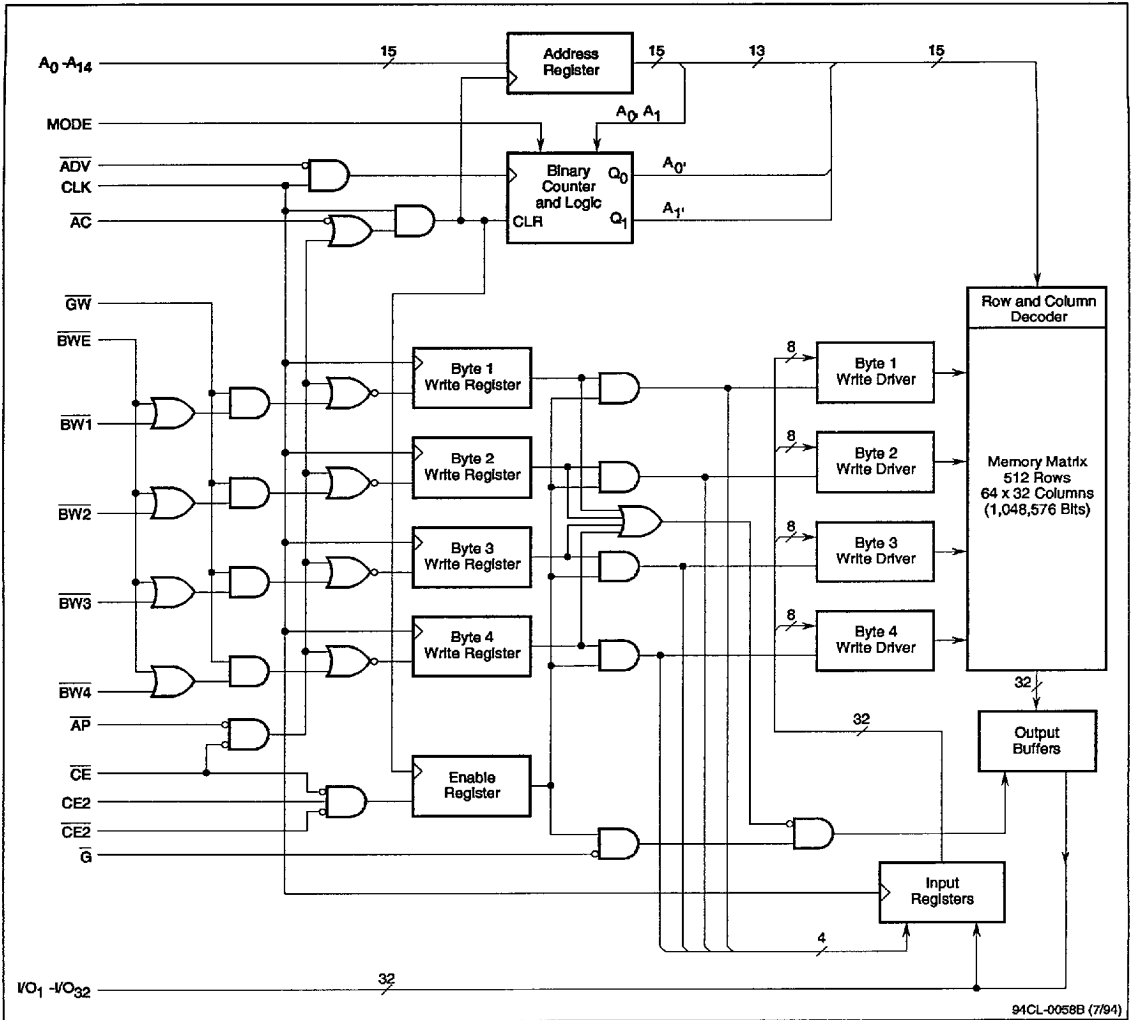
Operation	$\overline{G}$	I/O
Read Cycle	L	D <sub>OUT</sub>
	H	High-Z
Write Cycle	X	D <sub>IN</sub> , High-Z
Deselected	X	High-Z

X means don't care

### Partial Truth Table for Write Enables

Operation	$\overline{GW}$	$\overline{BWE}$	$\overline{BW1}$	$\overline{BW2}$	$\overline{BW3}$	$\overline{BW4}$
Read Cycle	H	H	X	X	X	X
	H	L	H	H	H	H
Write Cycle						
Byte 1 only	H	L	L	H	H	H
All bytes	H	L	L	L	L	L
All bytes	L	X	X	X	X	X

Block Diagram



## Absolute Maximum Ratings

*Supply voltage, $V_{DD}$	-0.5 to +4.6 V
*Input voltage, $V_{IN}$	-0.5 to +6.0 V
*Input/Output voltage, $V_{IO}$	-0.5 to +6.0 V
Operating temperature, $T_{OPR}$	0 to +70°C
Storage temperature, $T_{STG}$	-55 to +125°C

\* -2.5 V minimum (pulse width = 3 ns)

Exposure to Absolute Maximum Ratings for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The device should be operated within the limits specified under DC and AC Characteristics.

## Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	$V_{DD}, V_{DDQ}$	3.1	3.3	3.5	V
*Input voltage, low	$V_{IL}$	-0.5		0.8	V
Input voltage, high	$V_{IH}$	2.0		5.5	V
Ambient temperature	$T_A$	0		70	°C

\*-2.0 V minimum (pulse width = 2 ns).

## DC Characteristics

$T_A = 0$  to +70°C;  $V_{DD} = +3.3 V \pm 0.2 V$ ; minimum transverse air flow = 2.5 meters/second

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input leakage current	$I_{LI}$	-2		2	μA	$V_{IN} = 0 V$ to $V_{DD}$
I/O leakage current	$I_{LO}$	-2		2	μA	$V_{IO} = 0 V$ to $V_{DD}$ ; output disabled
Operating supply current	$I_{DD}$			210	mA	Device selected; $f = 60$ MHz; $I_{IO} = 0$ ; (Note 1)
	$I_{DD1}$			45	mA	Suspend read cycle; $f = 60$ MHz; $I_{IO} = 0$ ; (Notes 1, 2)
Standby supply current	$I_{SB}$			20	mA	Device deselected; all inputs static; $f = 0$ MHz; (Note 1)
	$I_{SB1}$			2	mA	Device deselected; all inputs static; $f = 0$ MHz; (Note 3)
	$I_{SB2}$			50	mA	Device deselected; $f = 60$ MHz; (Note 1)
Output voltage, low	$V_{OL}$			0.4	V	$I_{OL} = 8$ mA
Output voltage, high	$V_{OH}$	2.4			V	$I_{OH} = -4$ mA

### Notes:

(1)  $V_{IN} \leq V_{IL}$  or  $\geq V_{IH}$

(2) AC, AP, ADV, GW, BWS  $\geq V_{IH}$

(3)  $V_{IN} \leq 0.2 V$  or  $\geq V_{DD} - 0.2 V$

## Capacitance

$T_A = +25^\circ C$ ;  $f = 1$  MHz;  $V_{IN}$  and  $V_{IO} = 0 V$

Parameter	Symbol	Min	Max	Unit
Input capacitance	$C_{IN}$		4	pF
Input/output capacitance	$C_{IO}$		7	pF

Note: Capacitance is sampled and not 100% tested.

**AC Characteristics, Read and Write Cycle**

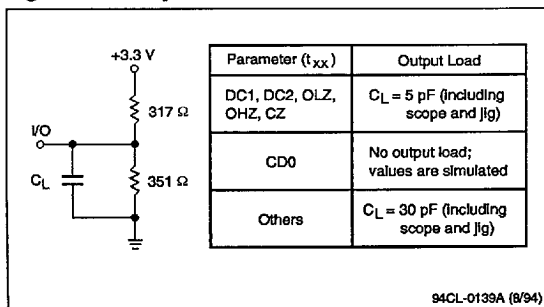
T<sub>A</sub> = 0 to +70°C; V<sub>DD</sub> = +3.3 V ±0.2 V

Parameter	Symbol		-10 (60 MHz)		-12 (50 MHz)		-14 (50 MHz)		Unit
	Standard	Alternate	Min	Max	Min	Max	Min	Max	
Cycle time	t <sub>KHKH</sub>	t <sub>CYC</sub>	16.7	—	20	—	20	—	ns
Clock access time	t <sub>KHQV0</sub>	t <sub>CD0</sub>	—	10	—	12	—	14	ns
	t <sub>KHQV</sub>	t <sub>CD</sub>	—	11	—	13	—	15	ns
Output enable to output valid	t <sub>GLQV</sub>	t <sub>OE</sub>	—	5	—	6	—	7	ns
Clock high to output active	t <sub>KHQX1</sub>	t <sub>DC1</sub>	6	—	6	—	6	—	ns
Clock high to output change	t <sub>KHQX2</sub>	t <sub>DC2</sub>	3	—	3	—	3	—	ns
Output enable to output active	t <sub>GLQX</sub>	t <sub>OLZ</sub>	2	—	2	—	2	—	ns
Output disable to output high-Z	t <sub>GHQZ</sub>	t <sub>OHZ</sub>	—	5	—	6	—	7	ns
Clock high to output high-Z	t <sub>KHQZ</sub>	t <sub>CZ</sub>	—	5	—	6	—	7	ns
Clock high pulse width	t <sub>KHKL</sub>	t <sub>CH</sub>	4	—	4	—	4	—	ns
Clock low pulse width	t <sub>KLKH</sub>	t <sub>CL</sub>	4	—	4	—	4	—	ns
Setup time									
Address	t <sub>AVKH</sub>	t <sub>AS</sub>	3	—	3	—	3	—	ns
Address status	t <sub>ADSVKH</sub>	t <sub>SS</sub>							
Data in	t <sub>DVKH</sub>	t <sub>DS</sub>							
Write enable	t <sub>WVKH</sub>	t <sub>WS</sub>							
Address advance	t <sub>ADVVKH</sub>								
Chip enable	t <sub>EVKH</sub>								
Hold time									
Address	t <sub>KHAX</sub>	t <sub>AH</sub>	0.5	—	0.5	—	0.5	—	ns
Address status	t <sub>KHADSX</sub>	t <sub>SH</sub>							
Data in	t <sub>KHDX</sub>	t <sub>DH</sub>							
Write enable	t <sub>KHWX</sub>	t <sub>WH</sub>							
Address advance	t <sub>KHADVX</sub>								
Chip enable	t <sub>KHEX</sub>								

**Test Conditions:**

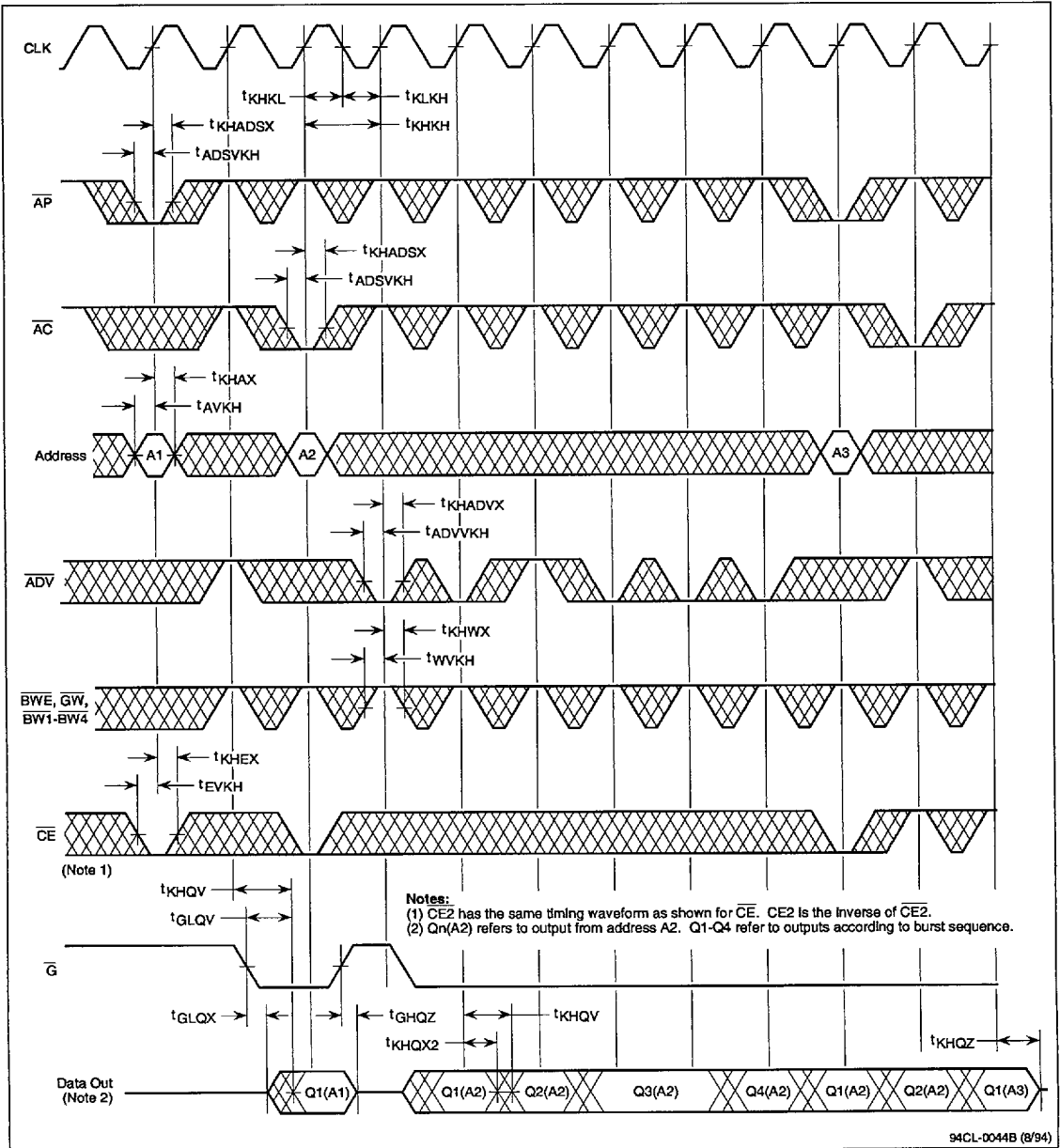
- (1) Input pulse: GND to 3 V with rise/fall times 1.5 ns.
- (2) Timing reference level: 1.5 V.
- (3) Output load: figure 1.
- (4) Minimum transverse air flow: 2.5 meters/second.

**Figure 1. Output Load**



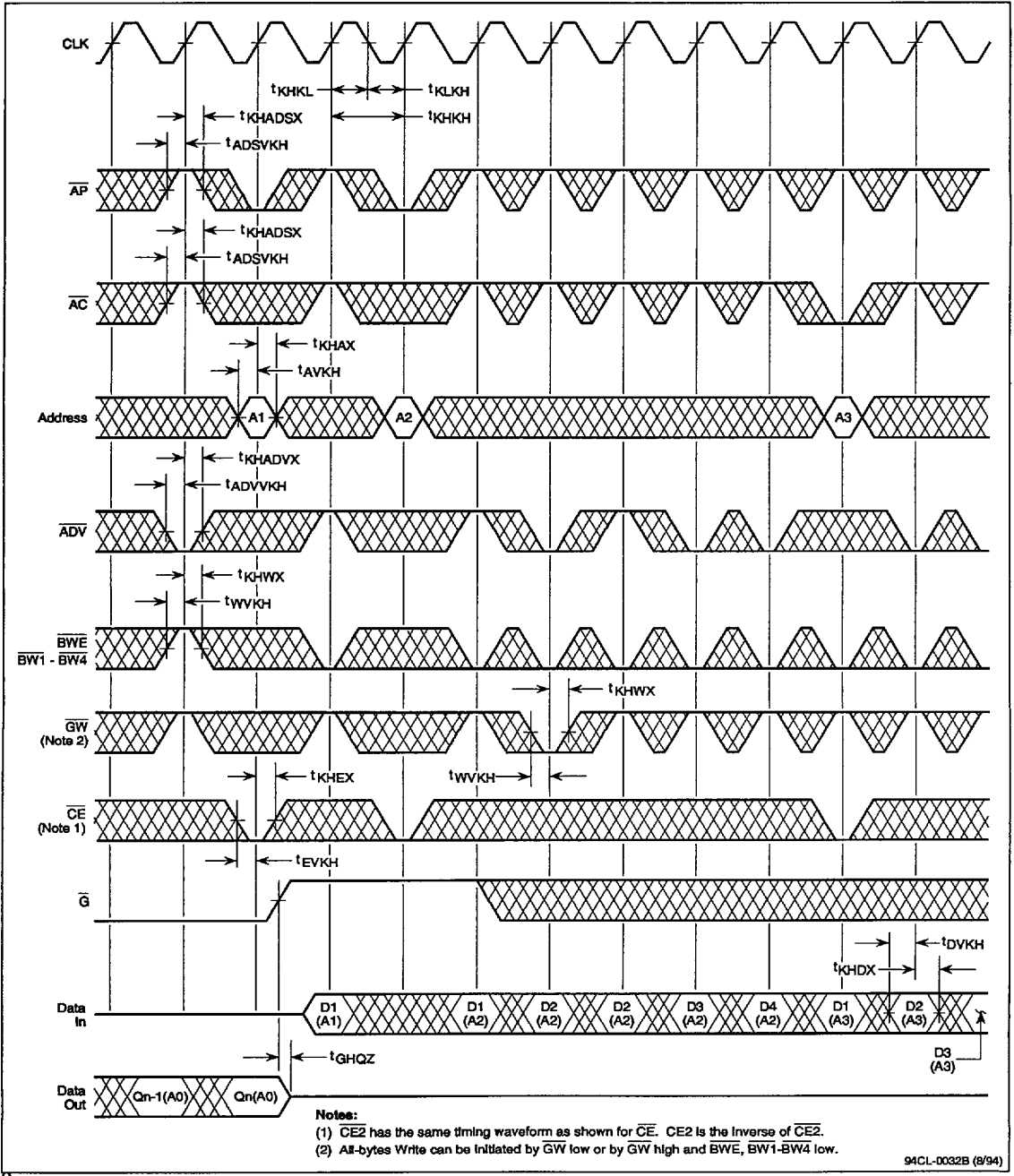
## Timing Waveforms

### Read Cycle



Timing Waveforms (cont)

Write Cycle

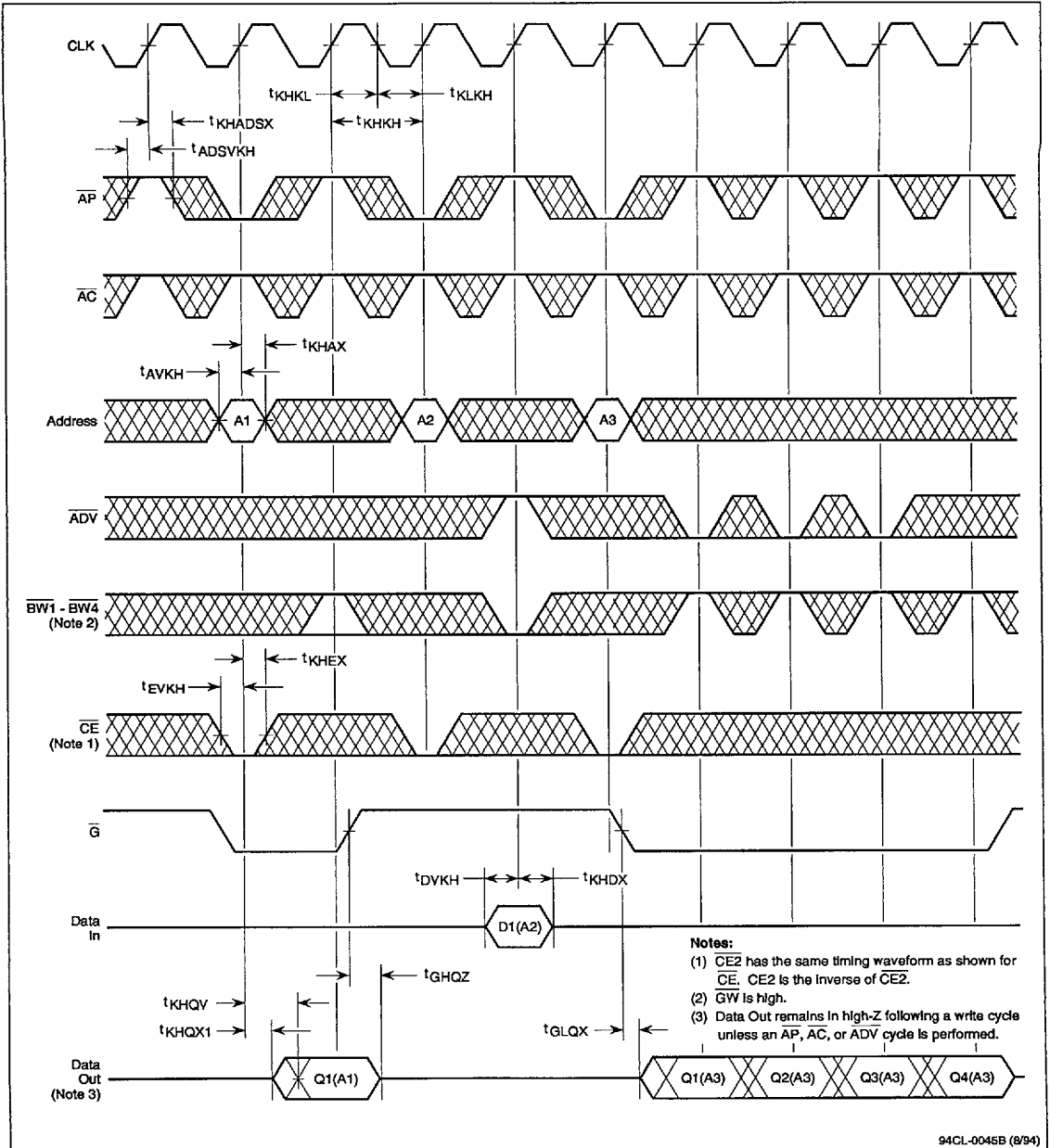


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## Timing Waveforms (cont)

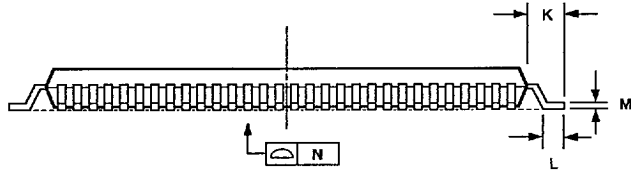
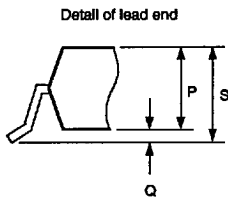
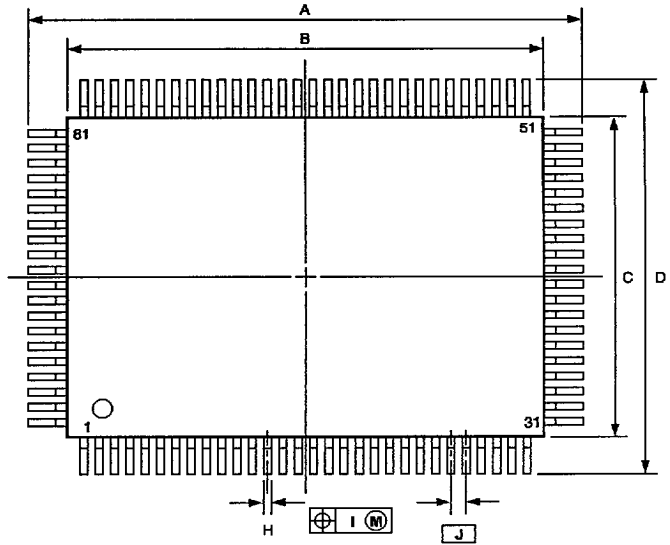
### Read/Write Cycle



Package Drawing

100-Pin TQFP

Item	Millimeters	Inches
A	22.0 ±0.3	.866 ±.012
B	20.0 ±0.2	.787 <sup>+0.009</sup> <sub>-.008</sub>
C	14.0 ±0.2	.551 <sup>+0.009</sup> <sub>-.008</sub>
D	17.8 ±0.4	.693 ±.016
H	0.32 <sup>+0.08</sup> <sub>-0.07</sub>	.013 <sup>+0.003</sup> <sub>-.003</sub>
I	0.13	.005
J	0.65 (TP)	.026 (TP)
K	1.0 ±0.2	.039 ±.008
L	0.5 ±0.2	.020 <sup>+0.009</sup> <sub>-.008</sub>
M	0.145 typ	.006 typ
N	0.1 typ	.004 typ
P	1.4 typ	.055 typ
Q	0.1 ±0.05	.004 ±.002
S	1.7 max	.067 max



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